

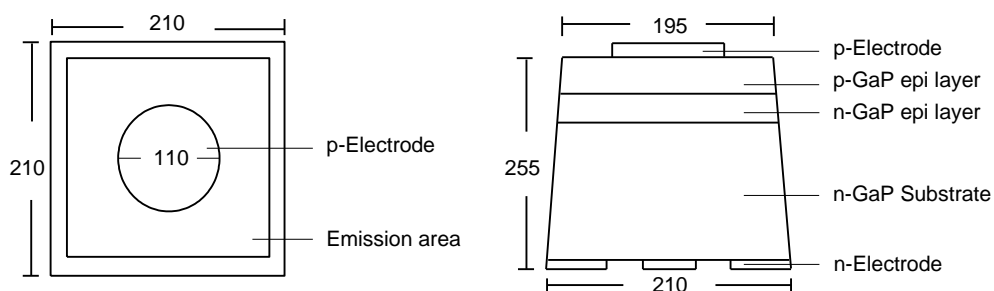
Features :

- GaP/GaP Epi Wafer

Typical Applications :

- Lamp
- SMD
- Display
- Dot Matrix

Outline Dimensions : (Unit: μm)



Physical Structure :

Chip dimension	Chip size	210 μm x 210 μm
	Thickness	255 μm
	Emission area	195 μm
	Bonding pad	110 μm
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	1.80	2.30	2.60	V
Reverse Current	I_R	$V_R = 5 \text{ V}$	-	-	10	μA
Wavelength	λ_P	$I_F = 20 \text{ mA}$	-	568	-	nm
	Hue		569	572	574	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	30	-	nm
Luminous Intensity	I_v	$I_F = 20 \text{ mA}$	6.0	-	-	mcd

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

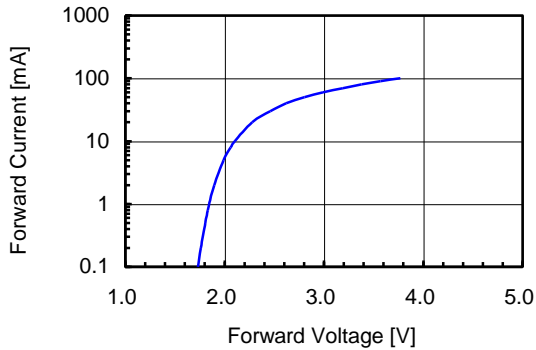


Fig 2. Relative Intensity vs. Forward Current

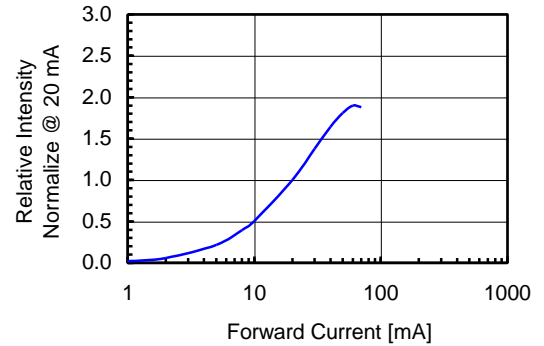


Fig 3. Forward Voltage vs. Temperature

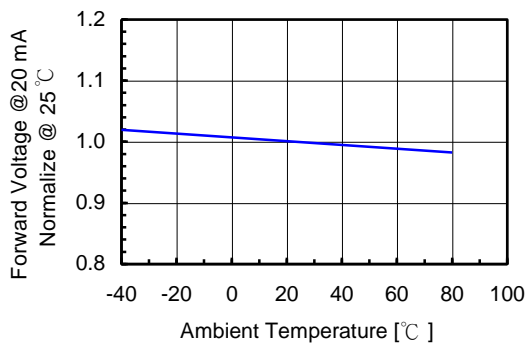


Fig 4. Relative Intensity vs. Temperature

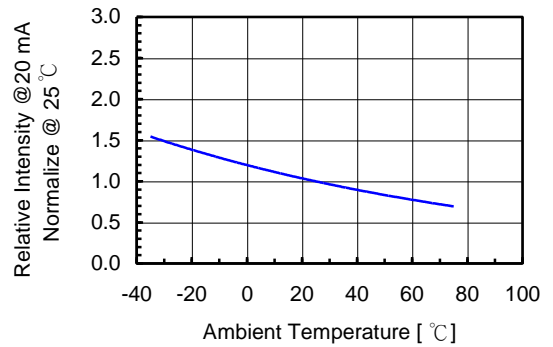


Fig 5. Relative Intensity vs. Wavelength

